a second dielectric material having a second dielectric constant different from the first dielectric constant,

the first and second dielectric materials being scalable for a set of feature size technologies,

the set of feature size technologies defined by a gate length in the range of 25-150nm, and

wherein the first material thickness and the second material thickness are determined by the relationship

$$t_1/k_1 + t_2/k_2 = t_{ox}/k_{ox}$$

wherein t_1 is the first material thickness,

t_2 is the second material thickness,

t_{ox} is the minimum thickness for a gate dielectric of silicon dioxide for a chosen gate length,

k_1 is the dielectric constant for the first dielectric material,

k_2 is the dielectric constant for the second dielectric material, and

k_{ox} is the dielectric constant of silicon dioxide.

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15. (Four Times Amended) An apparatus comprising:

a semiconductor substrate having a transistor device formed thereon, the transistor device having a gate dielectric disposed directly between a surface of the substrate and a gate electrode comprising:

a first dielectric material having a first dielectric constant; and

a second dielectric material having a second dielectric constant different from the first dielectric constant,

the first and second dielectric materials being scalable for each of a plurality of feature size technologies, having a gate length in the range of 25-150nm, and

wherein the first material thickness and the second material thickness are determined by the relationship

$$t_1/k_1 + t_2/k_2 = t_{ox}/k_{ox}$$

wherein t_1 is the first material thickness,

t_2 is the second material thickness,

t_{ox} is the minimum thickness for a gate dielectric of silicon dioxide for a chosen gate length,

k_1 is the dielectric constant for the first dielectric material,

k_2 is the dielectric constant for the second dielectric material, and

k_{ox} is the dielectric constant of silicon dioxide.